TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM12G45,SM12J45,SM12G45A,SM12J45A

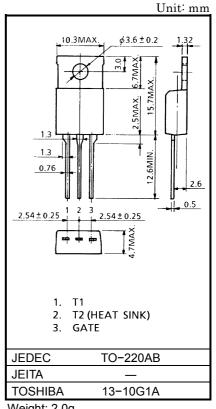
AC POWER CONTROL APPLICATIONS

• R.M.S On-State Current $: I_{T (RMS)} = 12A$

• High Commutating (dv / dt)

MAXIMUM RATINGS

CHARACTERIS	SYMBOL	RATING	UNIT		
Repetitive Peak Off-State Voltage	SM12G45 SM12G45A	V	400	V	
	SM12J45 SM12J45A	V_{DRM}	600		
R.M.S On-State Current (Full Sine Waveform Tc =	I _{T (RMS)}	12	Α		
Peak One Cycle Surge On-State		l	120 (50Hz)	А	
Current (Non-Repetitive))	I _{TSM}	132 (60Hz)	Α	
I ² t Limit Value (t = 1~10n	ı ² t	72	A ² s		
Critical Rate of Rise of O Current	di / dt	50	A / μs		
Peak Gate Power Dissipa	P_{GM}	5	W		
Average Gate Power Dis	P _{G (AV)}	0.5	W		
Peak Gate Voltage	V_{GM}	10	V		
Peak Gate Current	I _{GM}	2	Α		
Junction Temperature	Tj	-40~125	°C		
Storage Temperature Ra	T _{stg}	-40~125	°C		



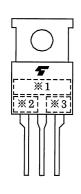
Weight: 2.0g



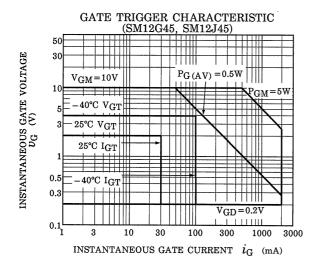
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

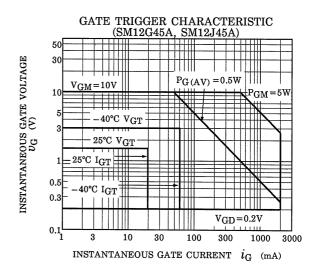
CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT		
Repetitive Peak	Peak Off-State Current I _{DRM} V _{DRM} =Rated, T _j = 125°C		Γ _j = 125°C	_	_	2	mA			
Gate Trigger Voltage SM		M12G45 M12J45	I	- V _{GT}	$V_D = 12V$, $R_L = 20\Omega$	T2 (+) , Gate (+)		_	2	V
	SM12		II			T2 (+) , Gate (-)	_	_	2	
	SM12		III			T2 (-) , Gate (-)		_	2	
			IV			T2 (-) , Gate (+)	_	_	_	
		SM12G45A SM12J45A	I			T2 (+) , Gate (+)	_	_	1.5	
	SM12		II			T2 (+) , Gate (-)	_	_	1.5	
	SM12		III			T2 (-) , Gate (-)	_	_	1.5	
			IV			T2 (-) , Gate (+)	_	_	_	
Gate Trigger Current SM		SM12G45 SM12J45	I	Іст	V _D = 12V, R _L = 20Ω	T2 (+) , Gate (+)		_	30	- mA
	SM12		II			T2 (+) , Gate (-)	_	_	30	
	SM12		III			T2 (-) , Gate (-)	_	_	30	
			IV			T2 (-) , Gate (+)	_	_	_	
		SM12G45A SM12J45A	I			T2 (+) , Gate (+)	_	_	20	
	SM12		II			T2 (+) , Gate (-)	_	_	20	
	SM12		III			T2 (-) , Gate (-)		_	20	
						T2 (-) , Gate (+)		_	_	1
Peak On-State Voltage		V _{TM}	I _{TM} = 17A			_	1.5	V		
Gate Non-Trigger Voltage		V _{GD}	V _D = Rated, Tc = 125°C		0.2	_	_	V		
Holding Current		I _H	V _D = 12V, I _{TM} = 1A			_	50	mA		
Thermal Resistance		R _{th (j-c)}	Junction to Case, AC			_	1.8	°C/W		
Critical Rate of Rise of Off-State Voltage at Commutation SM12G45 SM12J45 SM12G45A SM12J45A			(-1 / -14.)	V _{DRM} = 400V		10	_	_	V/ue	
				(dv / dt) c $(di / dt) c = -6.5$		5A / ms	4	_	_	- V / μs

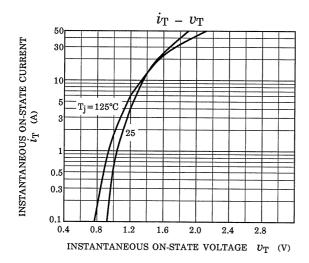
MARKING

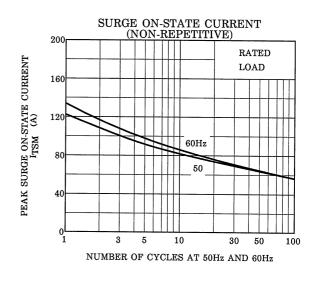


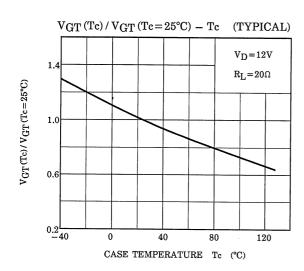
1	ı			
NUMBER	SYMBOL		MARK	
*1		SM12G45, SM12G45A	M12G45	
	TYPE	SM12J45, SM12J45A	M12J45	
*2		SM12G45A, SM12J45A	A	
*3	Lot Number Month (Starting from Alphabet A) Year (Last Decimal Digit of the Current Year)		Example 8A : January 1998 8B : February 1998 8L : December 1998	

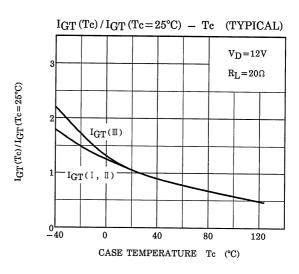


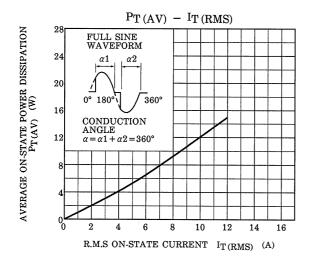


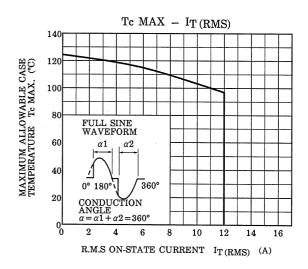


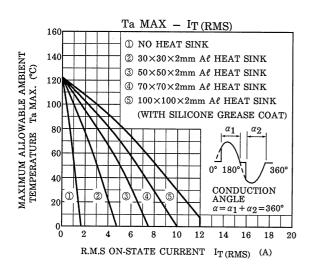


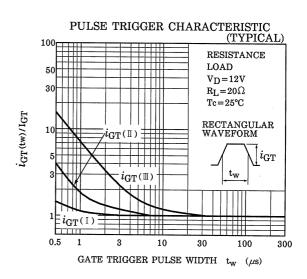


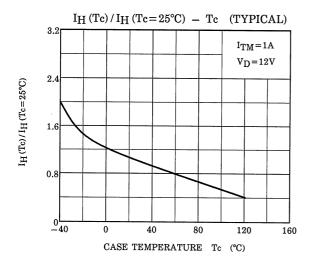


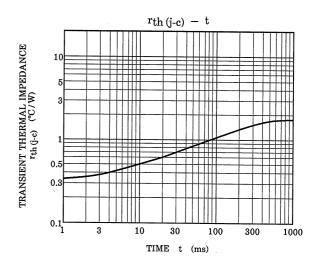












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